

ERC and SRC Applications In Practical PCB Design Process

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2016/07/06



Abstract

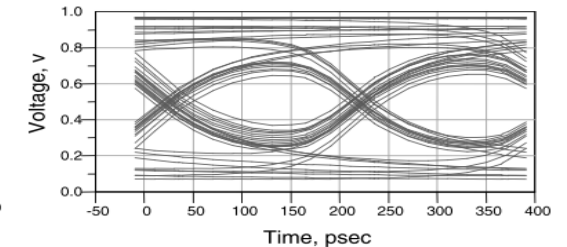
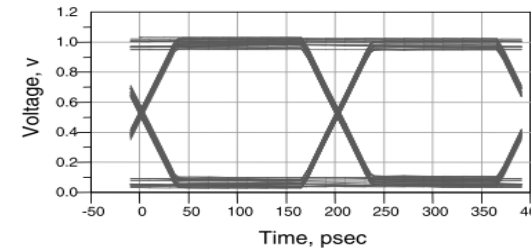
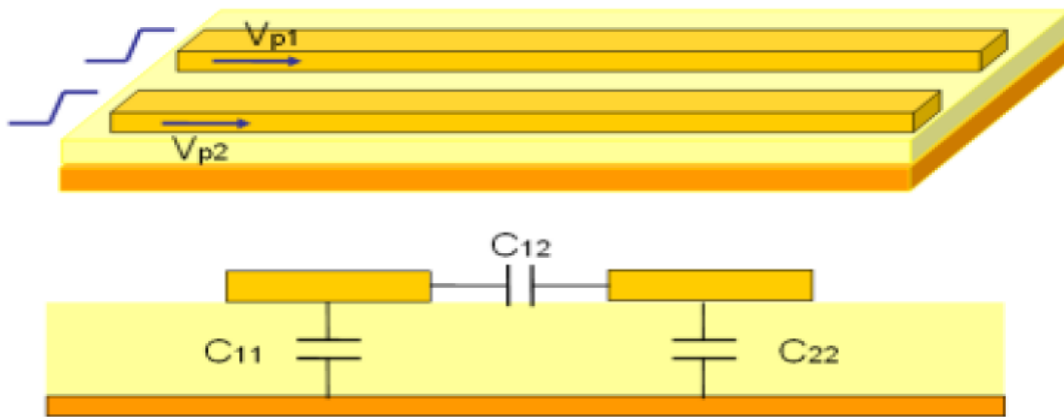
- **Overview**
- ERC (Electrical Rule Check)
- SRC (Simulation Rule Check)
- Applications
- Summary

Overview

- **No models** required : easy to run by PCB layout designers
- Detects **impedance discontinuities** of routed PCB signals
- Detects **excessive coupling** between routed PCB signals
- Integrated with OrCAD PCB Designer for easy modification of problem signals

Theoretical Background ERC

Coupling is defined with Near-ended Crosstalk as a victim.



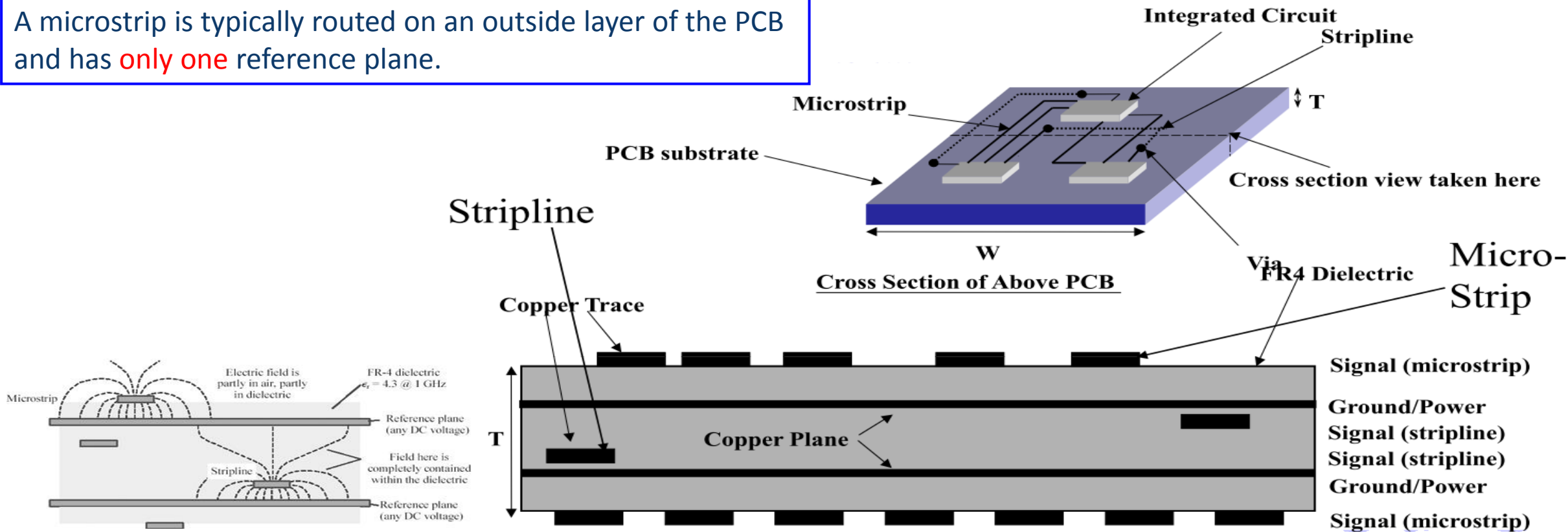
Eye diagrams of a 5-Gbps pseudorandom bit stream. Left: little loss. Right: same bit pattern when there is a lot of loss, showing the collapse of the eye diagram, and increased jitter, indicated by the widening of the cross-over regions.

1. Radiative loss
2. Coupling to adjacent traces
3. Impedance mismatches ★
4. Conductor loss
5. Dielectric loss

⇒
Reflection noise
Crosstalk noise
Power and ground noise

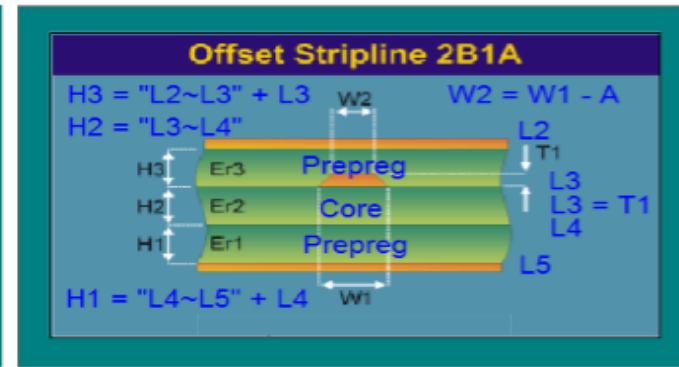
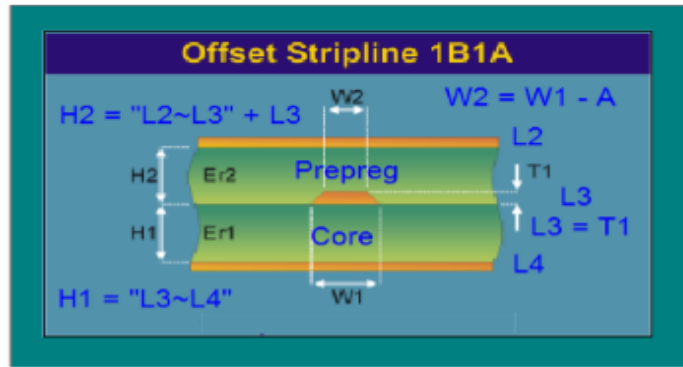
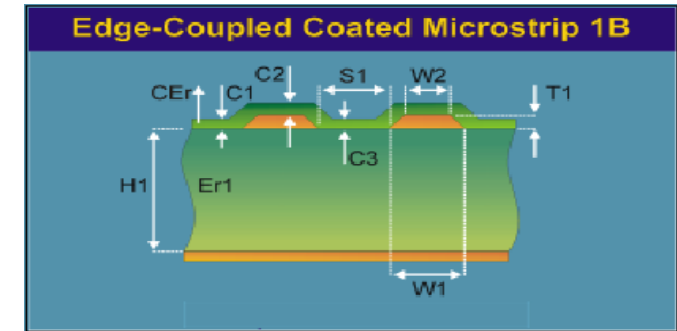
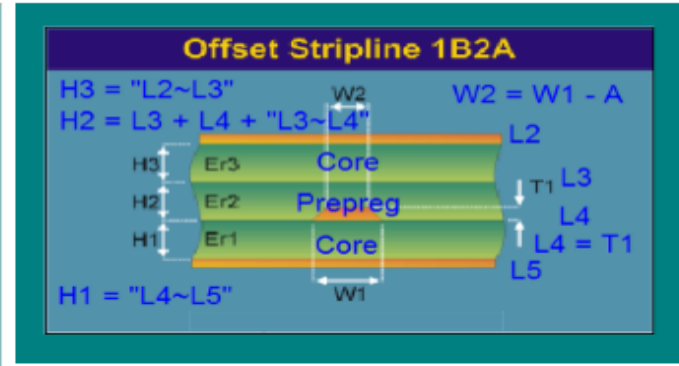
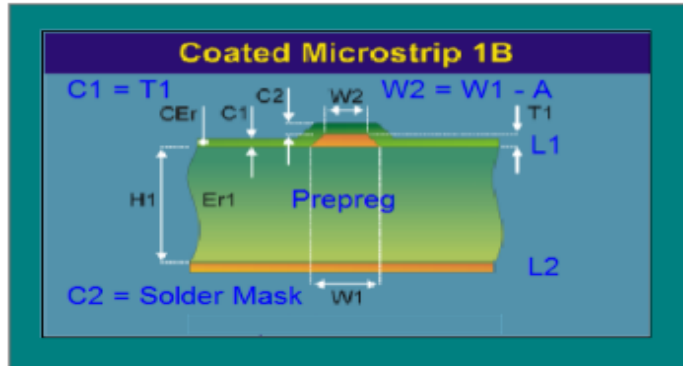
Impedance Discontinuities

A microstrip is typically routed on an outside layer of the PCB and has **only one** reference plane.



A stripline is routed on an inside layer and has **two** reference planes.

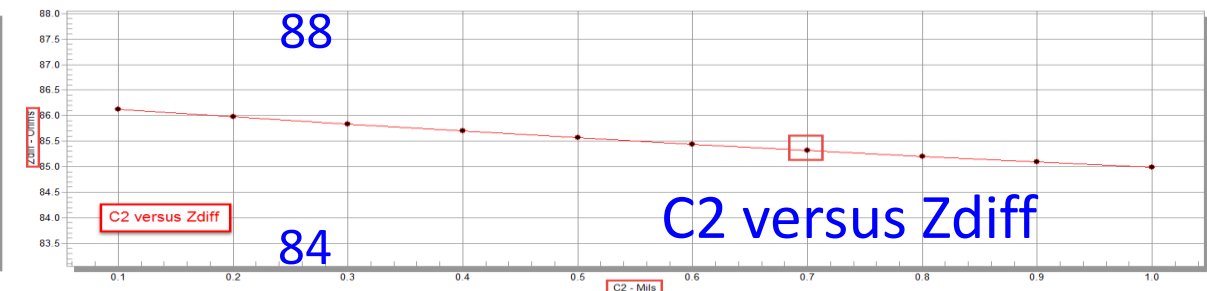
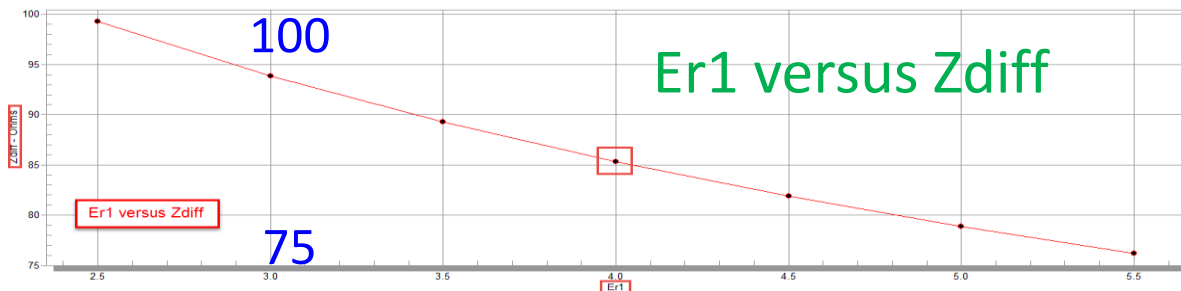
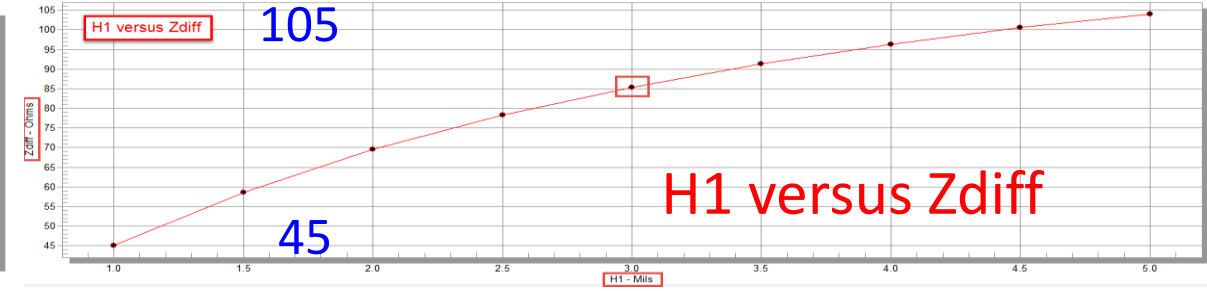
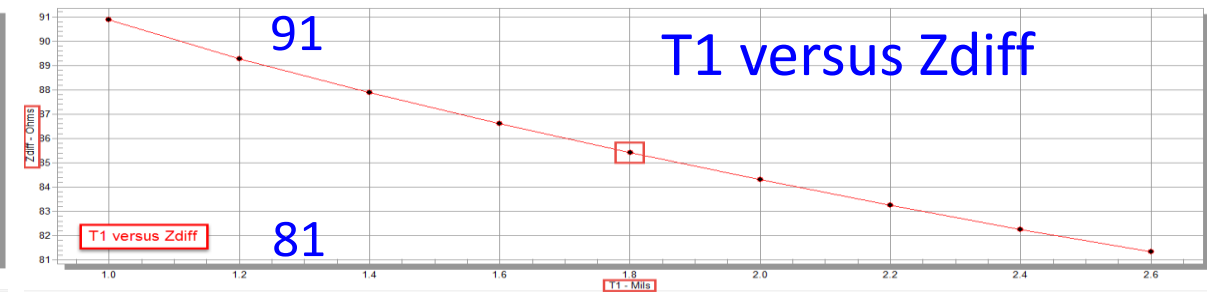
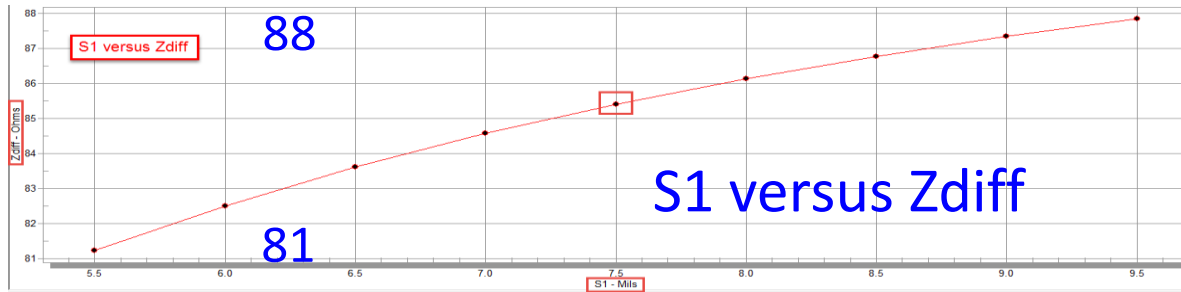
Impedance Discontinuities



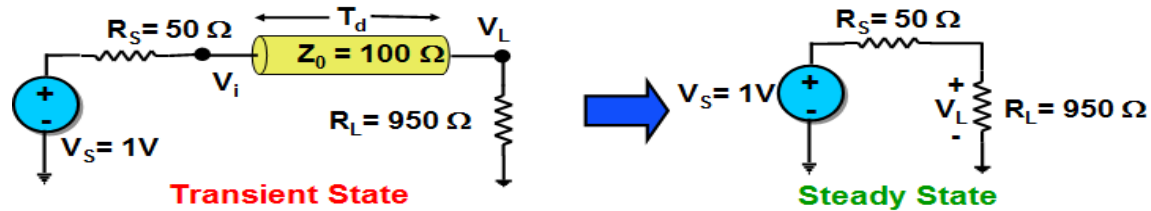
PCB stack up- 6 Layer T=93 mil

	S/M 1.2		
	Base cu+plating 1.4 mil		Layer 1
	Prepreg 5mil		
	Cu 1.4 mil		Layer 2
	Core 31 mil H/H oz(Exclude cu)		
	Cu 1.4 mil		Layer 3
	Prepreg 5mil		
	Cu 1.4 mil		Layer 4
	Core 31mil H/H oz(Exclude cu)		
	Cu 1.4 mil		Layer 5
	Prepreg 5mil		
	Base cu+plating 1.4 mil		Layer 6
	S/M 1.2		
	Board Thickness 87.8		MIL

Impedance Discontinuities



Impedance Discontinuities



$$\rho_s = \frac{R_s - Z_0}{R_s + Z_0}$$

$$= \frac{50 - 100}{50 + 100}$$

$$= -0.33$$

$$\rho_L = \frac{R_L - Z_0}{R_L + Z_0}$$

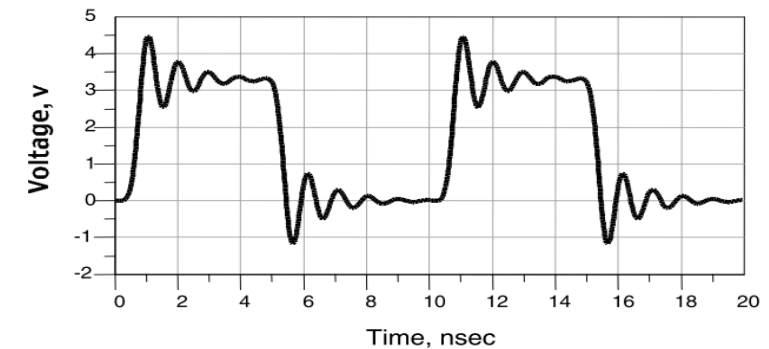
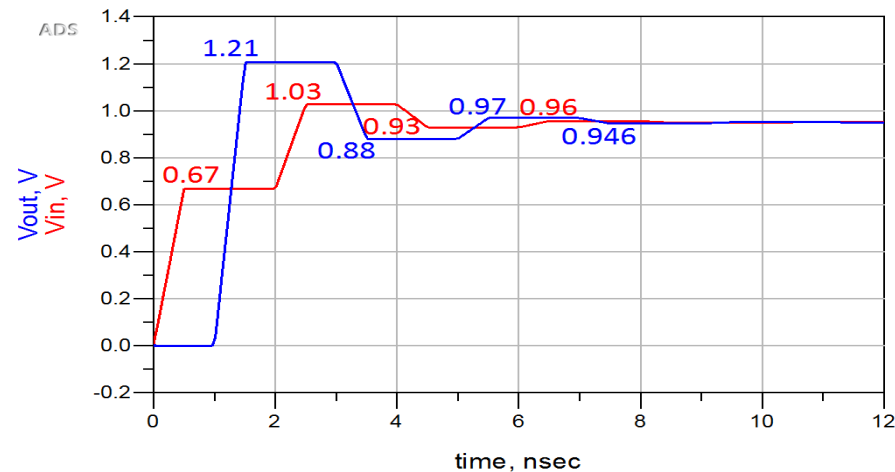
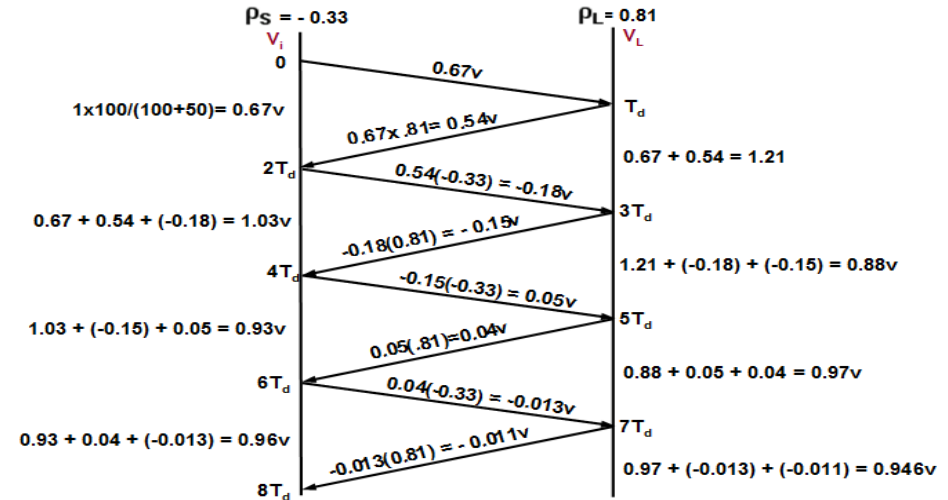
$$= \frac{950 - 100}{950 + 100}$$

$$= 0.81$$

$$V_{L\text{-steady}} = \frac{R_L}{R_s + R_L} V_s$$

$$= \frac{950}{50 + 950} 1V$$

$$= 0.95 V$$



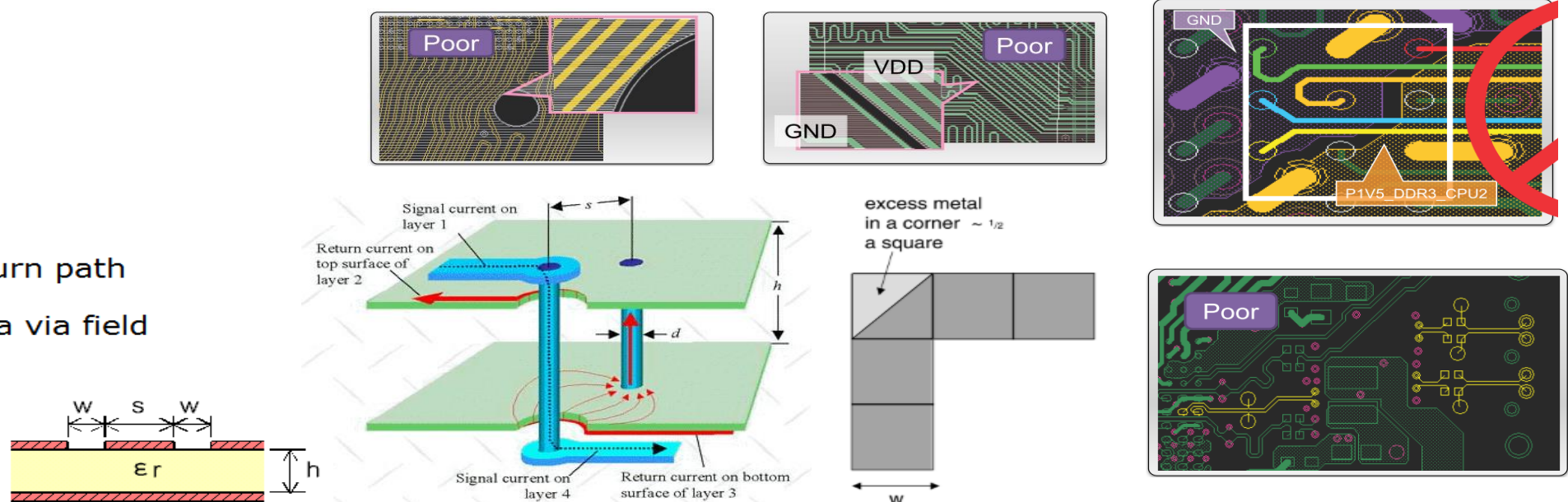
"Ringing" noise at the receiver end of a 1-inch-long controlled-impedance interconnect created because of impedance mismatches and multiple reflections at the ends of the line.

Impedance Discontinuities

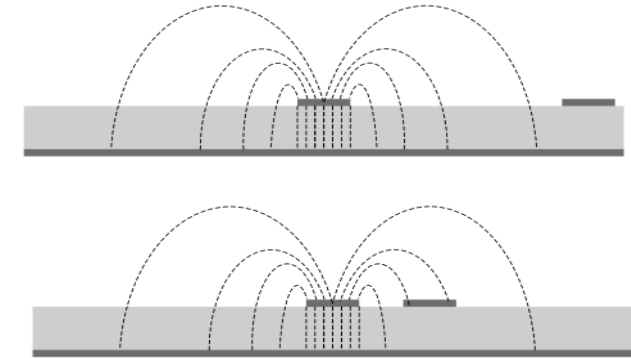
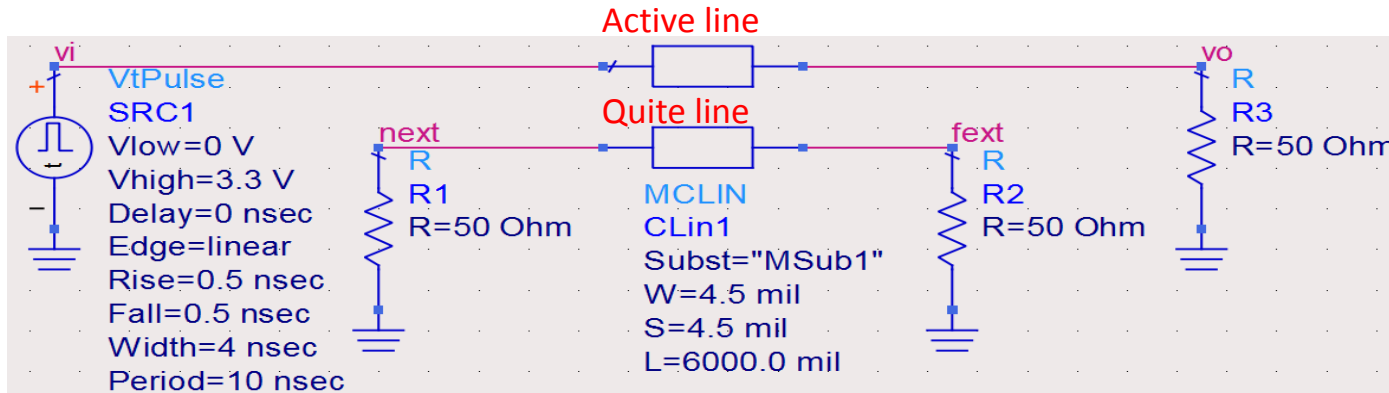
Even if a circuit board is designed with controlled-impedance interconnects, there is still the opportunity for a signal to see an impedance discontinuity from such features as:

1. The ends of the line
2. A package lead
3. An input-gate capacitance
4. A via between signal layers
5. A corner
6. A stub
7. A branch
8. A test pad
9. A gap in the return path
10. A neck down in a via field
11. A crossover

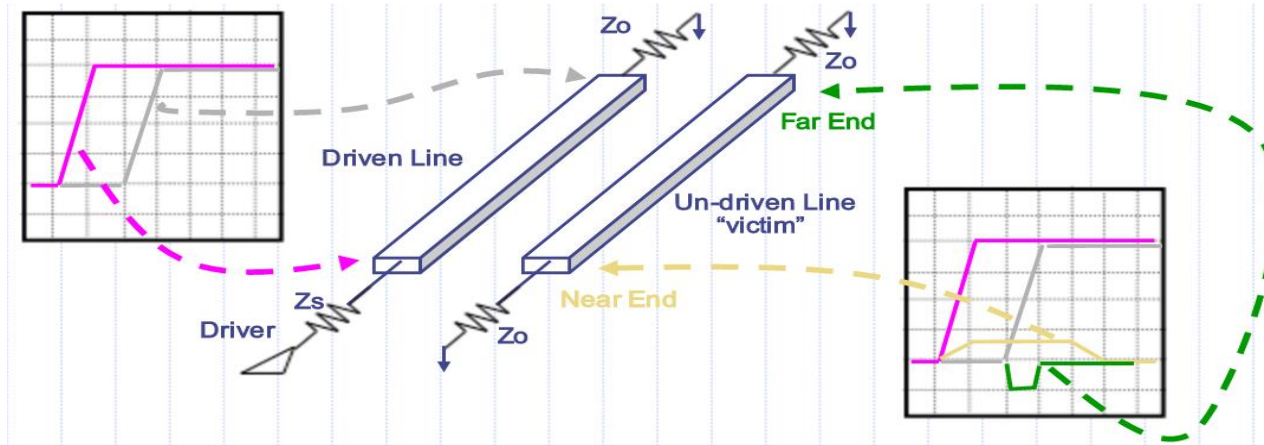
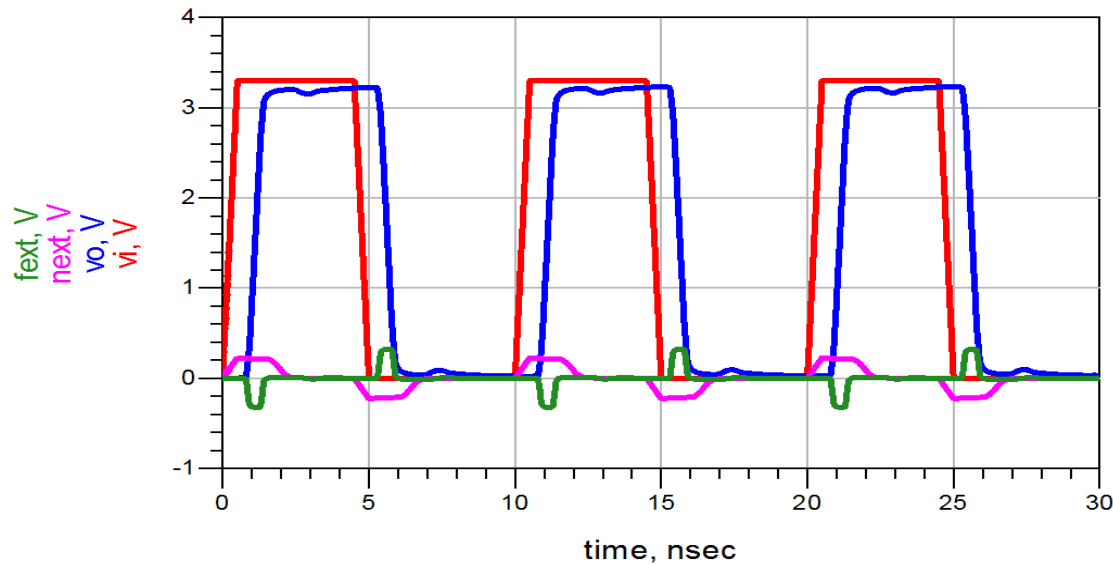
Unless otherwise specified, as a rough rule of thumb, the reflection noise level should be kept to less than **10% of the voltage swing**. For a 3.3-v signal, this is 330 mV of noise.



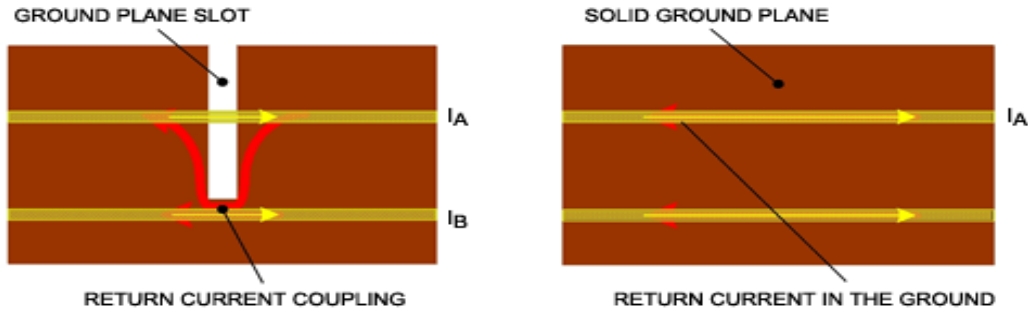
Excessive Coupling



Fringe fields near a signal line. When a second trace is far away, there is little fringe-field coupling and little cross talk. When the second net is in the vicinity of the fringe fields, there can be excessive coupling and cross talk.



Excessive Coupling



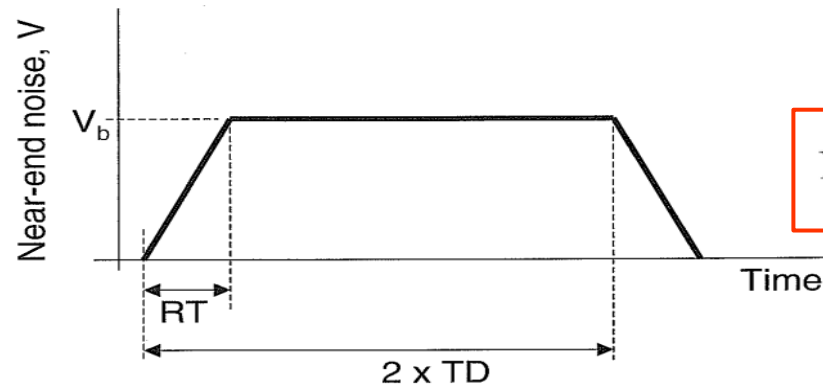
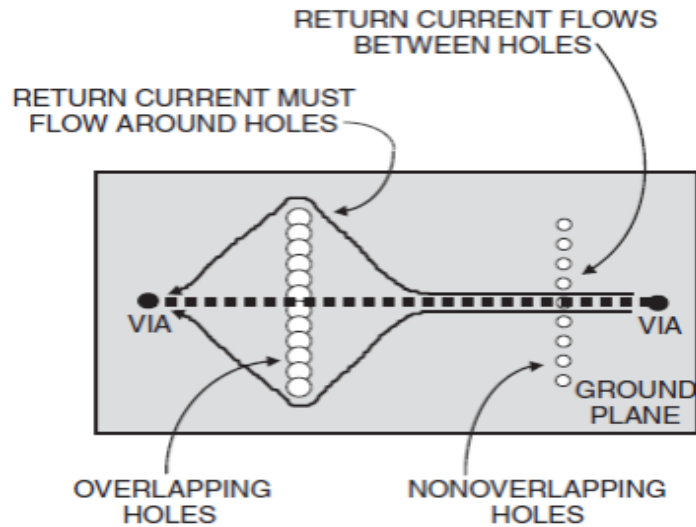
$$\text{Len}_{\text{sat}} = \frac{1}{2} \times \text{RT} \times v \sim \text{RT} \times 3 \frac{\text{inch}}{\text{nanosecond}}$$

where:

Len_{sat} = the saturation length for near-end cross talk, in inches

RT = the rise time of the signal in nsec

v = the speed of the signal down the active line in inches/nsec

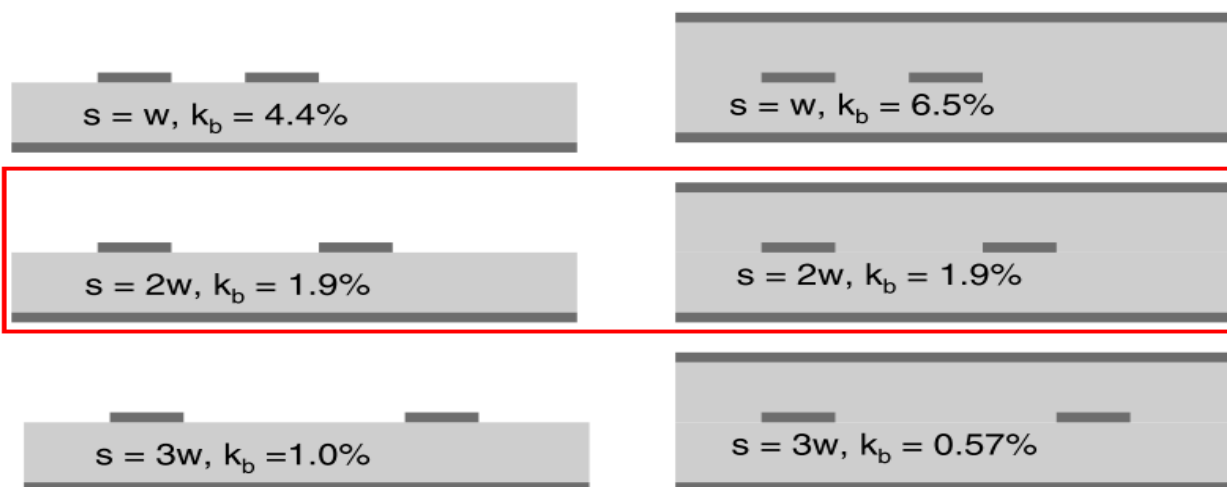


$$\text{NEXT} = \frac{V_b}{V_a} = k_b = \frac{1}{4} \left(\frac{C_{mL}}{C_L} + \frac{L_{mL}}{L_L} \right)$$

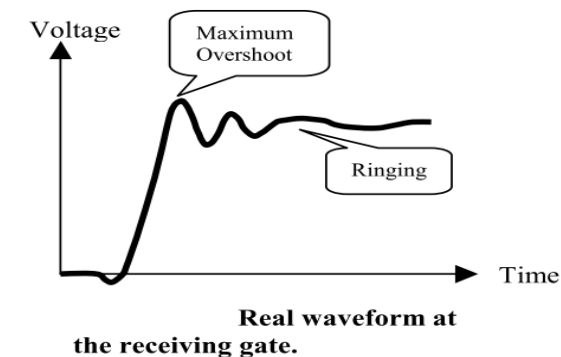
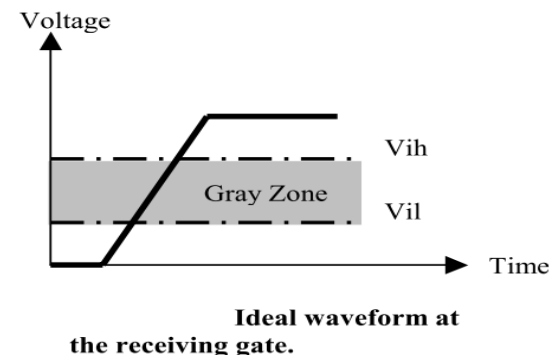
Near-end cross-talk voltage signature when the signal is a linear ramp.

Excessive Coupling

5-mil-wide 50 ohm line in microstrip and stripline



Near-end cross-talk coefficients for microstrip and stripline for a few specific spacings. These are handy rules of thumb to remember.



In **single-ended systems**, the maximum amount of crosstalk to design for, from all sources, should be less than about **5% of the signal swing**. In **high speed serial links**, a safe value for the maximum crosstalk to design for should be less than **-50dB, or 0.3%**.

Excessive Coupling

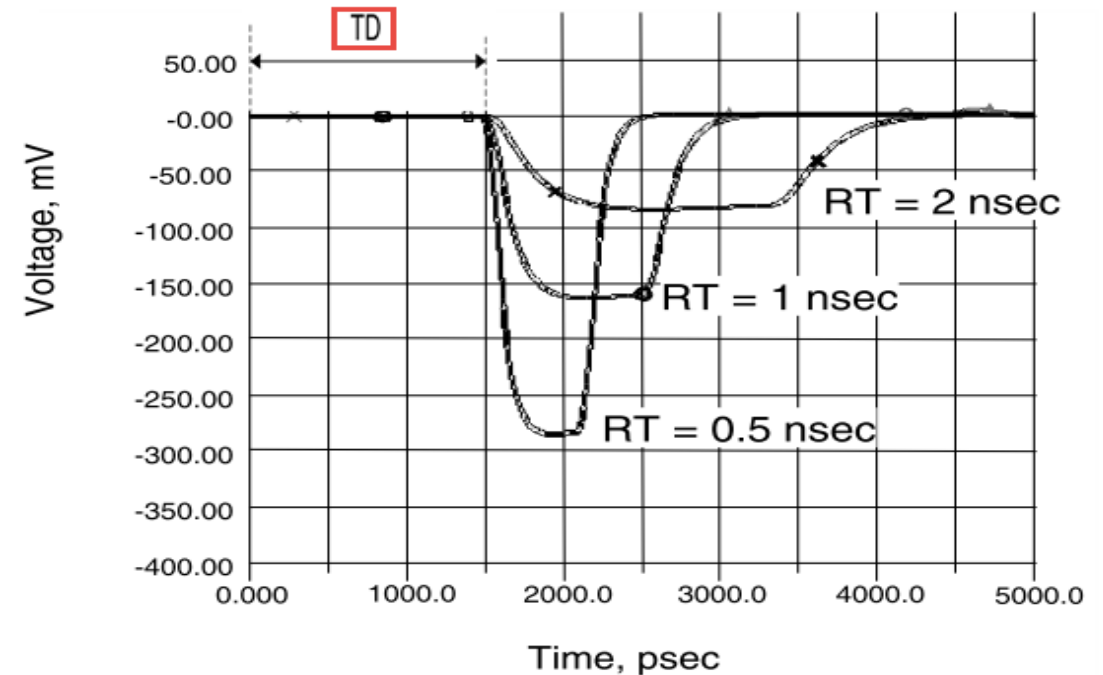
5-mil-wide 50 ohm line in microstrip

$$s = w, v \times k_f = -4.0\%$$

$$s = 2w, v \times k_f = -2.2\%$$

$$s = 3w, v \times k_f = -1.4\%$$

Simple rules of thumb for estimating the **far-end cross talk** for a pair of coupled 50-Ohm microstrips in FR4 for different spacings.



Far-end noise between two 50-Ohm microstrips in FR4 with 5-mil line and space, for the case of three different signal rise times, but the same 10-inch-long coupled length.

$$FEXT = \frac{V_f}{V_a} = \frac{Len}{RT} \times k_f = \frac{Len}{RT} \times \frac{1}{2v} \times \left(\frac{C_{mL}}{C_L} - \frac{L_{mL}}{L_L} \right)$$

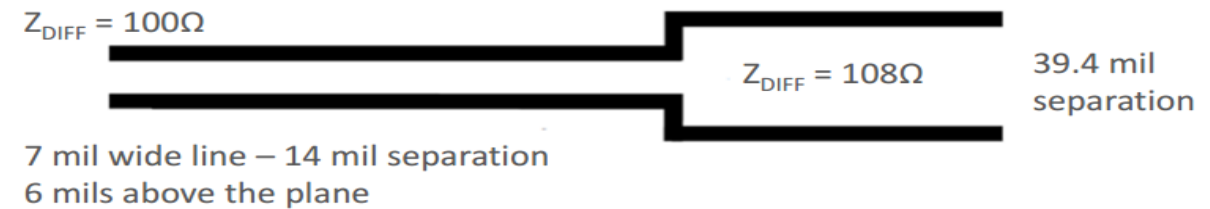
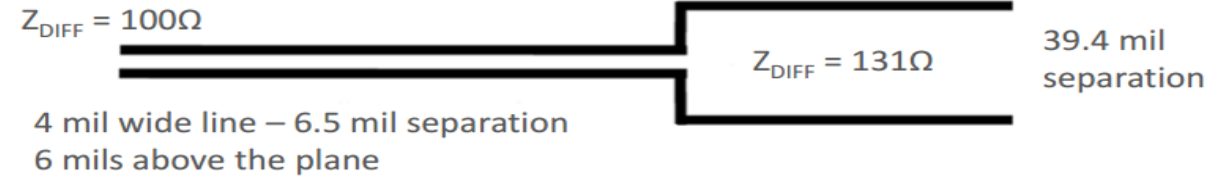
Excessive Coupling



Non-Interleaved



Interleaved

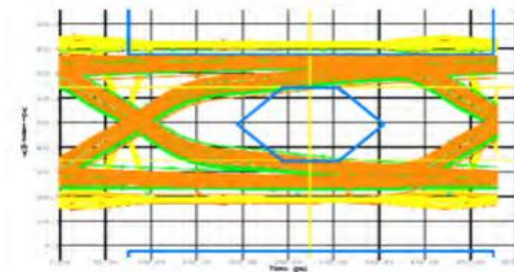


Interleaved mode is implemented on microstrip when FEXT is more significant than NEXT.

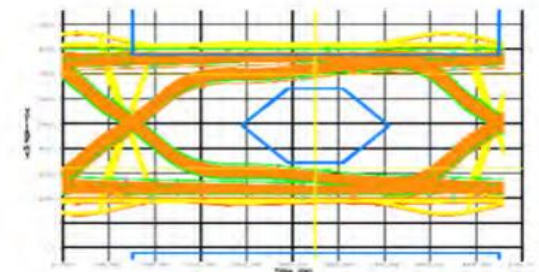
On the other hand, non-interleaved routing is implemented stripline when NEXT is more significant than FEXT.

[Signal Integrity Challenges and Design Practices on a Mobile Platform]

24" long microstrip traces example



4 mil wide traces – 3.125Gb/s



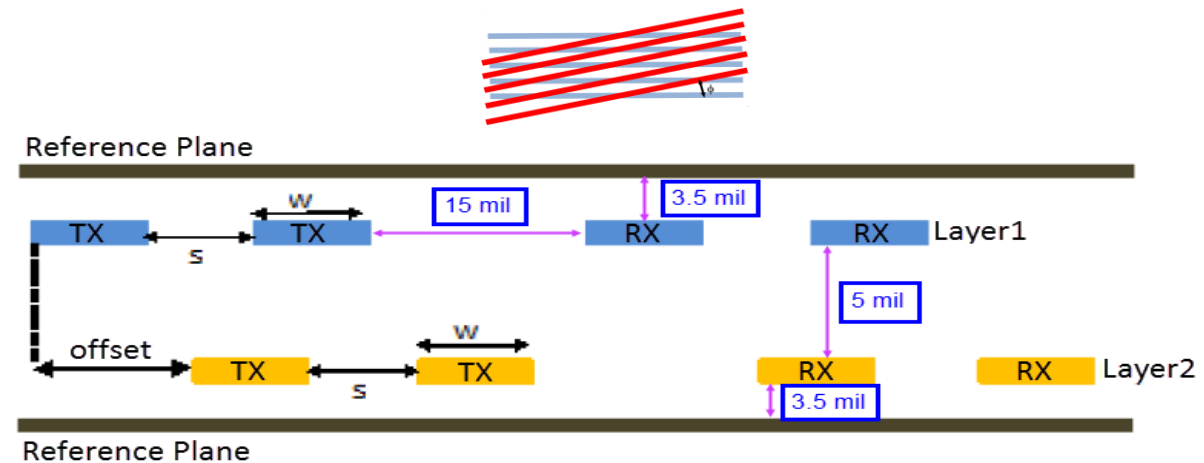
7 mil wide traces – 3.125Gb/s

Excessive Coupling

When **loss** is important, **loosely coupled** differential pairs should be used.

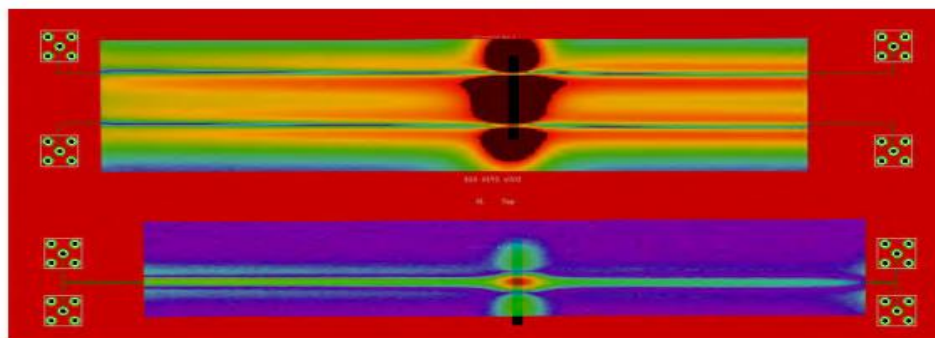
When interconnect **density** and noise **immunity** are important, **tightly coupled** differential pairs should be used.

With no overriding constraint, loose coupling with **a spacing equal to twice the trace width** offers a reasonable compromise in providing the lowest loss at the highest interconnect density.



For high frequency application, using **low DF solder mask** can help to decrease the microstrip insertion loss significantly, **~10% improvement** when comparing the traditional solder mask.

The optimum **coating thickness** for decreasing **far-end noise** will depend on all the geometry features and dielectric constants.



Loosely coupled vs. Tightly coupled differential pair with gap in return path

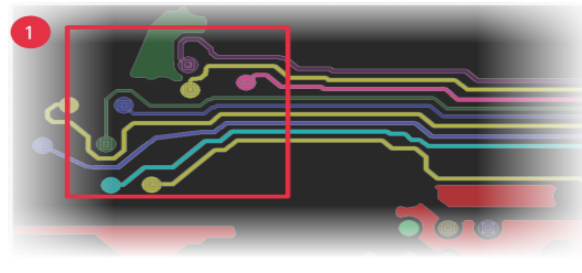
Abstract

- Overview
- **ERC (Electrical Rule Check)**
- SRC (Simulation Rule Check)
- Applications
- Summary

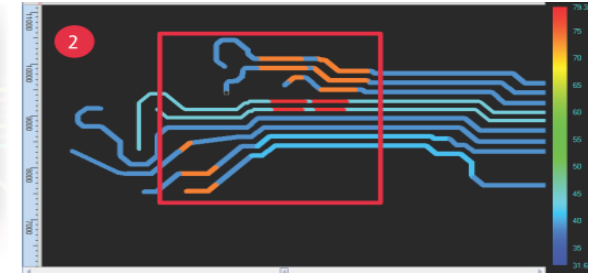
About ERC

ERC-based signal quality checks analyze at the individual, **segment-level** view in the **geometry domain** for signal quality, including:

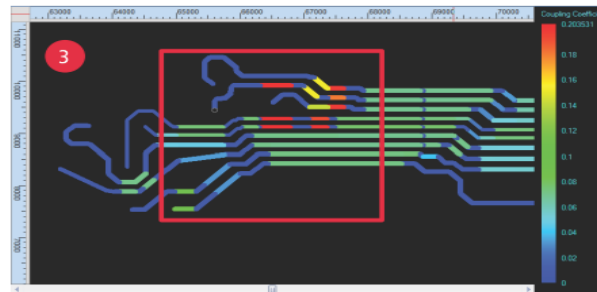
- Trace reference
- Trace reference-aware impedance
- Trace reference-aware coupling
- Differential pair routing phase
- Number of vias and via locations



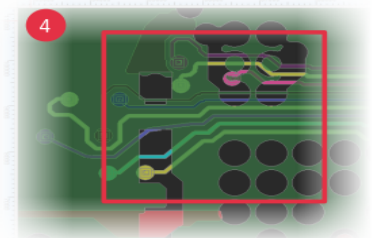
Layout view shows same trace impedance



OrCAD Sigrity ERC reference-aware impedance shows reference discontinuities



OrCAD Sigrity ERC reference-aware coupling shows increased coupling



...due to voids on reference planes

All analysis is organized for easy signal performance interpretation **by the PCB layout designer**, NOT the signal integrity (SI) expert.

About ERC

Trace coupling parameters

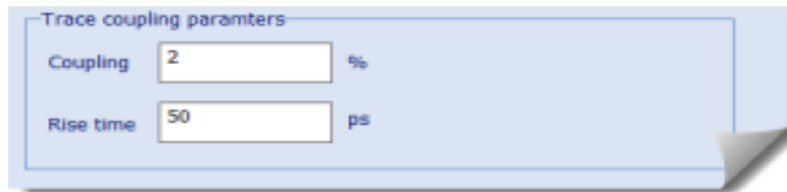
You can set up trace coupling parameters for the impedance/coupling/reference check. The trace coupling parameters will be used as a threshold. The trace couplings below this threshold will be ignored.

In order for trace coupling to be included,

- The trace near end coupling coefficients must be larger than the given value, and
- The coupled trace segment length must be longer than the NEXT saturation length. The saturation length is calculated using the rise time as

$$L_{saturation} = t_r * v$$

$$0.5 * Trise * V$$



Trace coupling parameters

Coupling %

Rise time ps

The smaller the coupling % and rise time thresholds, the more trace segments will be considered as coupled lines. This results in a longer simulation time.

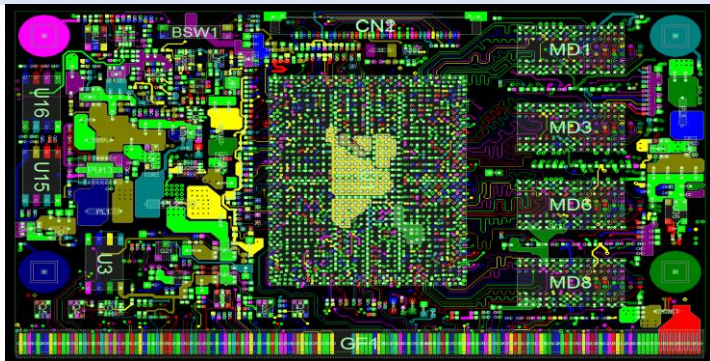
About ERC

Sigrity BrdExtractor

Settings

Translate MIXED layer to:

- Allow patches on signal layers
- Distinguish shapes of different nets by color
- Add pseudo plane(s) if lack of plane or patch
- Append net name to objects
- Include elements with no net names
- Create component model names based upon component part num
- Remove non-functional pads
- Translate antipads as voids
- Translate only voltage nets
- Treat pad on dielectric layer as drill
- Use "Board Geometry > Design Outline" for outline
- Generate via if padstack drill size is zero
- Calculate via plating using "Drill/Slot symbol" values
- Metal layer thickness as plating thickness



ERC - Trace Imp/Cpl/Ref Check

Layout Setup

- Load Layout File
- Check Stackup
- Prepare Nets

Simulation Setup

- Enable Trace Check Mode
 - Optional: Set up Net Groups
 - Optional: Show Net Groups
- Set up Trace Check Parameters
- Save File without Error Check

Simulation

Technology	Data rate	Fastest rise time	Scope BW
Ethernet 10base-T	10 Mbps	30 ns	600 MHz
Ethernet 100base-T	100 Mbps	3 ns	600 MHz
Ethernet 1000base-T	250 Mbps x 4	1.2 ns	1 GHz
USB 2.0	480 Mbps	300 ps	2.5 G
USB 3.0	5 Gbps	50 ps	12 GHz
DDR1	400 MT/s	500 ps	2 GHz
DDR2	1066 MT/s	250 ps	4 GHz
DDR3	2133 MT/s	100 ps	8 GHz
DDR4	3200 MT/s	75 ps	12 GHz
GDDR5	8 Gbps	30 ps	16 GHz
SATA 3G	3 Gbps	67 ps	12 GHz
SATA 6G	6 Gbps	33 ps	16 GHz
SAS-2	6 Gbps	42 ps	16 GHz
SAS-3	12 Gbps	21 ps	30 GHz
16G FibreChannel	14.025 Gbps	24 ps	35 GHz
HDMI 1.4	3.4 Gbps	50 ps	8 GHz
DisplayPort 1.2	5.4 Gbps	50 ps	13 GHz

Impedance/Coupling Check Option

- Impedance
- Coupling Coefficient

Trace coupling paramters

Coupling %

Rise time ps

Nets Selection Option

- Check all signal nets(enable all signal nets)
- Check all enabled signal nets
- Check by NetGroup

Notes: Go to Net Manager to enable nets for Trace Check

Notes:
 1.Detailed and interactive results are available with Check by NetGroup.
 2.A pair of extended nets are reported as one signal.

Coplanar Traces

- Detect and model the coplanar traces

About ERC

Net count	Net name	Trace Name	Imp(Ohm)	Length (mil)	Trace Delay (ps)	(x,y) Location - (mil)	Layer	R (mOhm)	L (nH)	C (pF)
1	G_DDIO_TX0_N	Trace11409::X_PCIEX1_TX1_P_C	53.7	11.453	1.6	(1455.049;247.951)	Signal\$AW_L10	1.652	0.088	0.030
2	G_DDIO_TX0_P	Trace11410::X_PCIEX1_TX1_P_C	53.7	4.961	0.7	(1459.098;241.421)	Signal\$AW_L10	0.716	0.038	0.013
3	X_PCIEX1_TX1_N	Trace11410::X_PCIEX1_TX1_P_C	52.4	0.012	0.0	(1459.098;238.935)	Signal\$AW_L10	0.002	0.000	0.000
4	X_PCIEX1_TX1_N_C	Trace11410::X_PCIEX1_TX1_P_C	44.5	7.039	1.0	(1459.098;235.409)	Signal\$AW_L10	1.015	0.045	0.023
5	X_PCIEX1_TX1_P	Trace11411::X_PCIEX1_TX1_P_C	44.5	47.788	6.8	(1475.994;214.994)	Signal\$AW_L10	6.894	0.303	0.153
6	X_PCIEX1_TX1_P_C	Trace11412::X_PCIEX1_TX1_P_C	44.5	79.000	11.3	(1532.390;198.098)	Signal\$AW_L10	11.396	0.502	0.254
		Trace11413::X_PCIEX1_TX1_P_C	44.5	63.640	9.1	(1594.390;175.598)	Signal\$AW_L10	9.180	0.404	0.204
		Trace11414::X_PCIEX1_TX1_P_C	44.5	172.000	24.6	(1702.890;153.098)	Signal\$AW_L10	24.812	1.092	0.552
		Trace11415::X_PCIEX1_TX1_P_C	44.5	34.620	4.9	(1801.130;140.858)	Signal\$AW_L10	4.994	0.220	0.111
		Trace11416::X_PCIEX1_TX1_P_C	44.5	34.000	4.9	(1830.370;128.618)	Signal\$AW_L10	4.905	0.216	0.109
		Trace11417::X_PCIEX1_TX1_P_C	44.5	9.546	1.4	(1850.746;125.244)	Signal\$AW_L10	1.377	0.061	0.031
		Trace11417::X_PCIEX1_TX1_P_C	66.6	1.654	0.2	(1854.706;121.285)	Signal\$AW_L10	0.239	0.016	0.004
		Trace11418::X_PCIEX1_TX1_P_C	66.6	4.429	0.6	(1855.291;118.486)	Signal\$AW_L10	0.639	0.042	0.009
		Trace11419::X_PCIEX1_TX1_P_C	66.6	5.058	0.7	(1853.503;114.483)	Signal\$AW_L10	0.730	0.048	0.011
		Trace11419::X_PCIEX1_TX1_P_C	44.5	1.874	0.3	(1851.052;112.033)	Signal\$AW_L10	0.270	0.012	0.006
		Trace11420::X_PCIEX1_TX1_P_C	46.4	1.873	0.3	(1850.390;110.433)	Signal\$BOTTOM	0.162	0.013	0.006
		Trace11420::X_PCIEX1_TX1_P_C	96.7	45.127	6.1	(1850.390;86.933)	Signal\$BOTTOM	3.908	0.594	0.063
		Trace11421::X_PCIEX1_TX1_P_C	46.4	24.189	3.5	(1463.000;276.094)	Signal\$TOP	2.095	0.164	0.076
		Trace11422::X_PCIEX1_TX1_P_C	46.4	16.971	2.5	(1457.000;258.000)	Signal\$TOP	1.469	0.115	0.054
							PlanesL9_GND	76.453	3.971	1.709

About ERC

- File
 - General
 - File Manager
 - Save Options
 - Hotkeys
- Layout
 - Grid and Unit View
 - Processing
 - Trace
 - Error Checking
 - Translator
- 3D Layout View
 - Display
 - Quality
- Simulation (Basic)
 - General
 - Special Void
 - Radiation
 - Report
- Simulation (Advanced)
 - Electric Models
 - Field Solver
 - Reference Handling
 - Shape Options
 - Device Model
 - Temperature
 - Special Handling

Change the 'Processing' options

Polygon Simplification Threshold

0.1 mm

To simplify the polygons, select

Margin for Cut by Nets

Net count	Net name
1	G_DDIO_TX0_N
2	G_DDIO_TX0_P
3	X_PCIEX1_TX1_N
4	X_PCIEX1_TX1_N_C
5	X_PCIEX1_TX1_P
6	X_PCIEX1_TX1_P_C

Trace Name	Imp(Ohm)	Length (mil)	Trace Delay (ps)	(xy) Location - (mil)	Layer
Trace11409::X_PCIEX1_TX1_P_C	53.7	2.453	0.3	(1458.232;244.770)	Signal\$AW_L10
Trace11410::X_PCIEX1_TX1_P_C	53.7	4.961	0.7	(1459.098;241.421)	Signal\$AW_L10
Trace11410::X_PCIEX1_TX1_P_C	52.4	0.012	0.0	(1459.098;238.935)	Signal\$AW_L10
Trace11410::X_PCIEX1_TX1_P_C	44.5	7.039	1.0	(1459.098;235.409)	Signal\$AW_L10
Trace11411::X_PCIEX1_TX1_P_C	44.5	47.788	6.8	(1475.994;214.994)	Signal\$AW_L10
Trace11412::X_PCIEX1_TX1_P_C	44.5	79.000	11.3	(1532.390;198.098)	Signal\$AW_L10
Trace11413::X_PCIEX1_TX1_P_C	44.5	63.640	9.1	(1594.390;175.598)	Signal\$AW_L10
Trace11414::X_PCIEX1_TX1_P_C	44.5	172.000	24.6	(1702.890;153.098)	Signal\$AW_L10
Trace11415::X_PCIEX1_TX1_P_C	44.5	34.620	4.9	(1801.130;140.858)	Signal\$AW_L10
Trace11416::X_PCIEX1_TX1_P_C	44.5	34.000	4.9	(1830.370;128.618)	Signal\$AW_L10
Trace11417::X_PCIEX1_TX1_P_C	44.5	9.546	1.4	(1850.746;125.244)	Signal\$AW_L10
Trace11417::X_PCIEX1_TX1_P_C	66.6	1.654	0.2	(1854.706;121.285)	Signal\$AW_L10
Trace11418::X_PCIEX1_TX1_P_C	66.6	4.429	0.6	(1855.291;118.486)	Signal\$AW_L10
Trace11419::X_PCIEX1_TX1_P_C	66.6	0.933	0.1	(1854.961;115.943)	Signal\$AW_L10
Trace11420::X_PCIEX1_TX1_P_C	46.4	1.873	0.3	(1850.390;110.433)	Signal\$BOTTOM
Trace11420::X_PCIEX1_TX1_P_C	74.6	3.670	0.5	(1850.390;107.662)	Signal\$BOTTOM
Trace11420::X_PCIEX1_TX1_P_C	96.7	41.457	5.6	(1850.390;85.098)	Signal\$BOTTOM
Trace11421::X_PCIEX1_TX1_P_C	46.4	16.189	2.4	(1463.000;272.094)	Signal\$TOP
Trace11422::X_PCIEX1_TX1_P_C	45.9	10.971	1.6	(1459.122;260.120)	Signal\$TOP
TracePolygon31626::X_PCIEX1_TX1_P_C	49.6	1.627	0.2	(1850.390;114.057)	Signal\$BOTTOM
TracePolygon31626::X_PCIEX1_TX1_P_C	27.0	3.747	0.6	(1850.390;111.370)	Signal\$BOTTOM
TracePolygon31626::X_PCIEX1_TX1_P_C	49.6	3.670	0.5	(1850.390;107.662)	Signal\$BOTTOM
TracePolygon31626::X_PCIEX1_TX1_P_C	69.7	41.457	5.6	(1850.390;85.098)	Signal\$BOTTOM
TracePolygon31627::X_PCIEX1_TX1_P_C	69.7	37.280	5.0	(1850.390;45.730)	Signal\$BOTTOM
TracePolygon31627::X_PCIEX1_TX1_P_C	87.8	0.209	0.0	(1850.390;26.986)	Signal\$BOTTOM
TracePolygon31627::X_PCIEX1_TX1_P_C	-	13.012	-	(1850.390;20.376)	Signal\$BOTTOM
Total		637.234	88.3		

Via-AntiPads search: 0

DIMM Finger Pad Conversion

Convert DIMM finger pads to traces

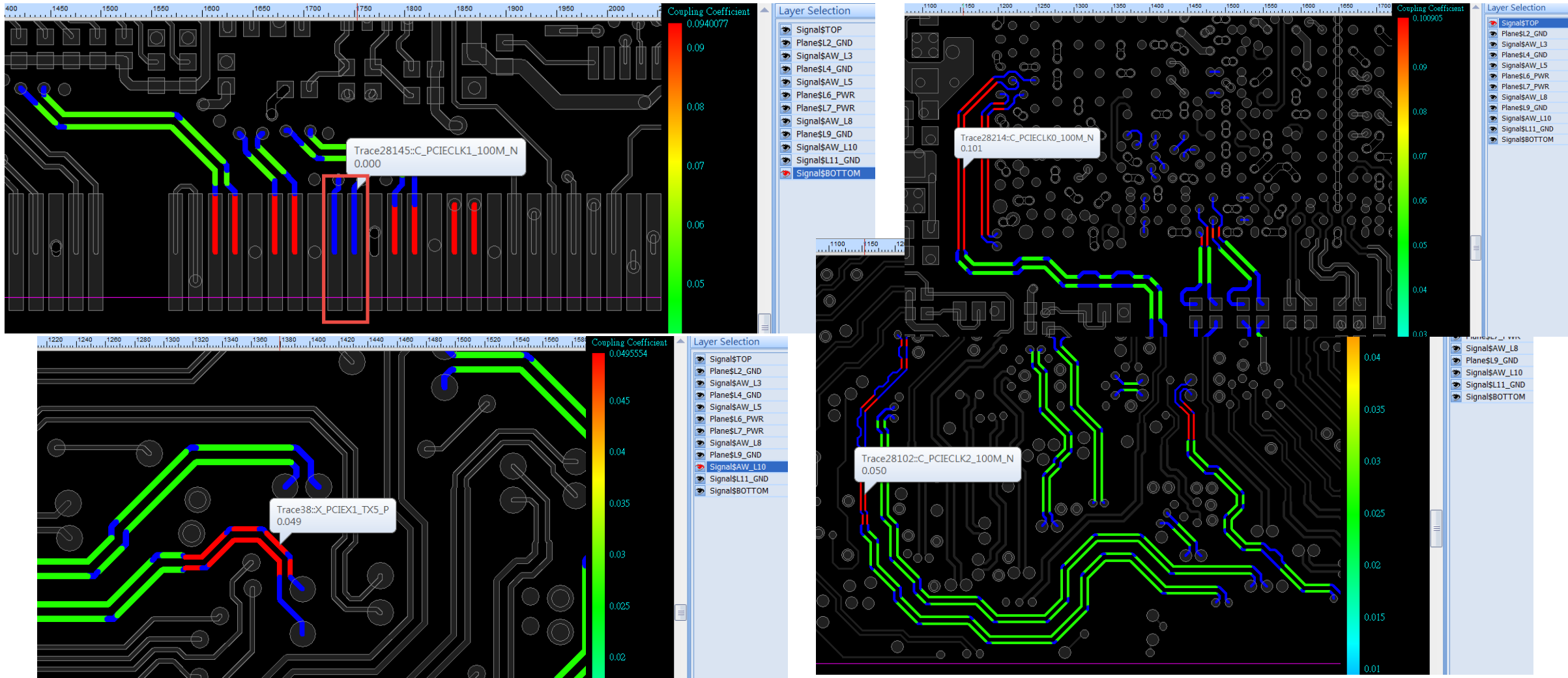
Pad <=> Shape Conversion

Max pad: 1 Min shape: 1 mil

Apply to: Power/Ground nets Signal nets

During shape processing, pads larger than the Max pad size (when not empty) are converted to shapes; solid shapes smaller than the Min shape size (when not empty) are converted to pads; and polygon pads with holes are always converted to shapes.

About ERC



About ERC

Is trace-to-trace coupling included in impedance calculation?

No.

Can trace impedance be determined only thru co-planar coupling?

For traces without reference planes, they may depend on the ground shapes on the same layer as signal return. Trace check impedance cannot be determined using co-planar coupling.

Are differential trace impedance and coupling check results available?

Starting from ASI 16.61, differential impedance and coupling are available. In order to get differential trace check results, differential nets need to be classified when forming net groups.

Is trapezoidal cross-section considered in the trace check?

Yes. You should use workflow step **Check Stackup** to set up trapezoidal angles.

About ERC

Is via impedance/coupling included in the trace check?

No.

Is via delay calculated in the trace check?

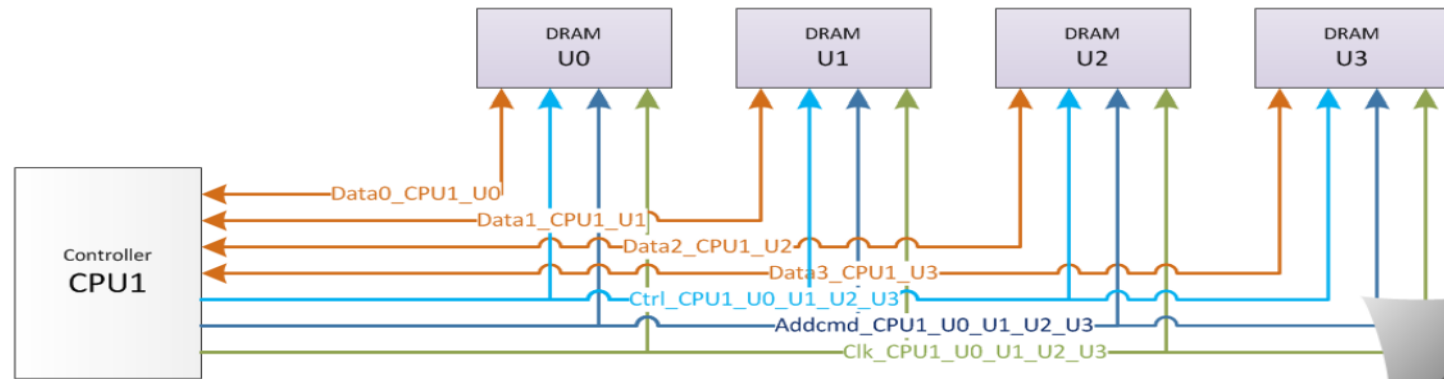
No.

Is coupling between different net groups included

If multiple net groups are included in one trace check simulation, **couplings among nets in all net groups are included.**

Is coupling for not enabled nets included?

No.



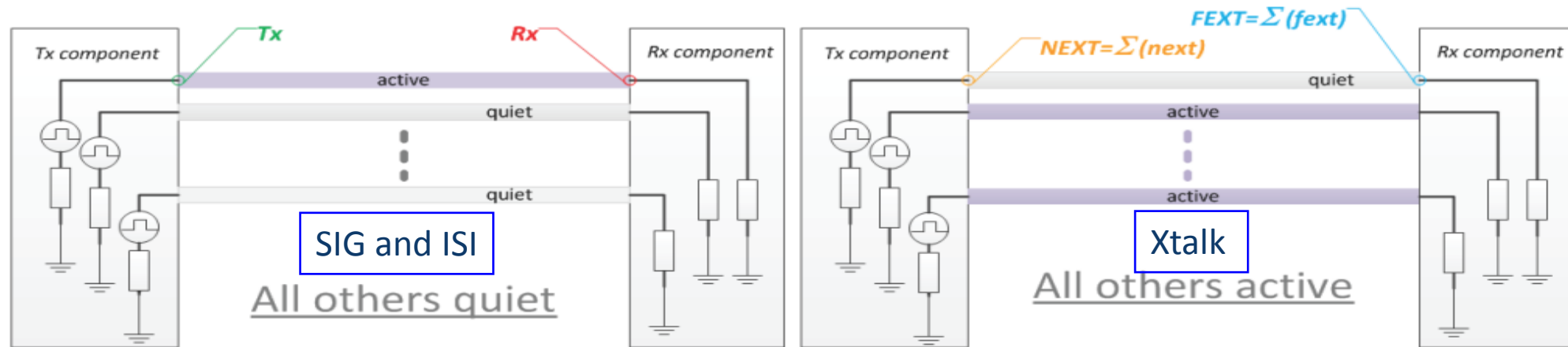
Abstract

- Overview
- ERC (Electrical Rule Check)
- **SRC (Simulation Rule Check)**
- Applications
- Summary

About SRC

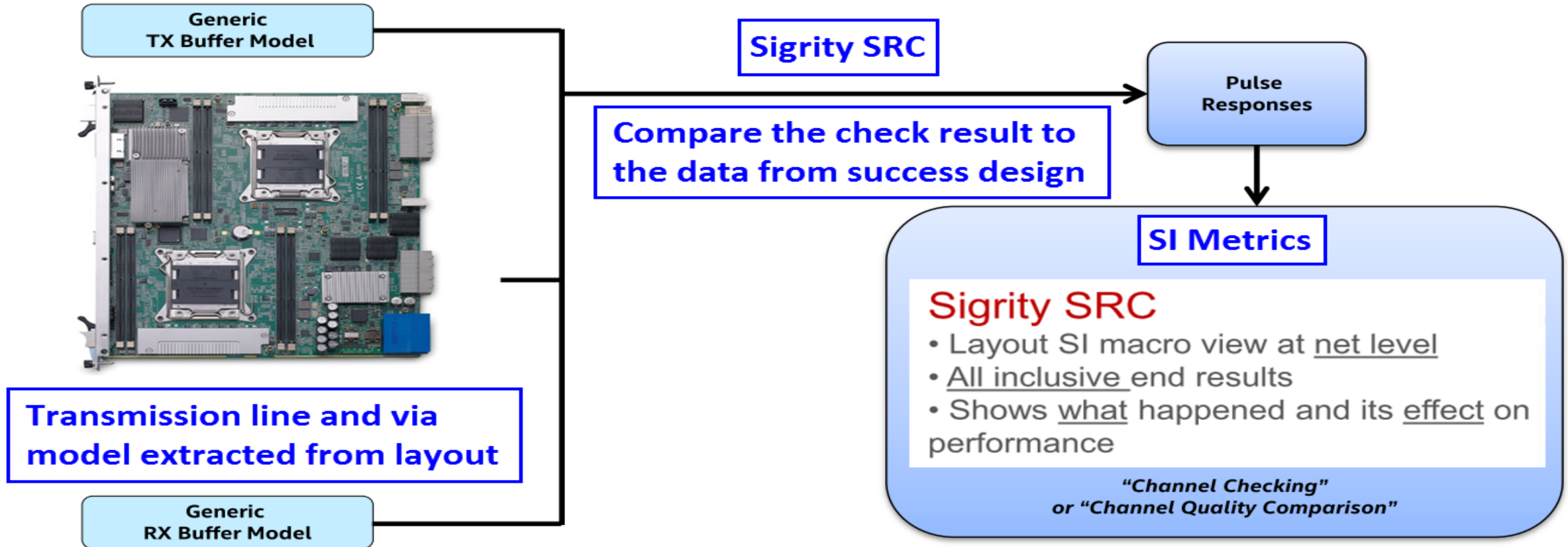
This **net-level** PCB layout checking engine is based on **time-domain simulation** (device simulation models are not needed), and considers:

- Loss
- Delay
- Reflections
- Trace couplings
- Via coupling



After SRC simulation, **TX**, **RX**, **NEXT** (near end xtalk), and **FEXT** (far end xtalk) waveforms are available, as well as **SI metrics** calculated using **RX** and **FEXT** waveforms as signal quality indicators.

About SRC



About SRC

$Int_sig = \int_{t_1}^{t_2} Rx(t) dt$	Higher channel loss will decrease the SIG. Trace length, dielectric loss, and conductive loss will all increase the channel loss. <i>The higher SIG, the better signal integrity is.</i>
$Int_ISI = \int_0^{t_1} Rx(t) dt + \int_{t_2}^{t_{max}} Rx(t) dt$	Loss and impedance discontinuity will both increase the "ISI" (Intersymbol interference). <i>The larger the ISI, the worse signal integrity is.</i>
$Int_xtk = \sum \int_0^{t_{max}} fext_i(t) dt$	Far-end crosstalk is calculated by including all the other signals which is included in the simulation. <i>The larger FEXT, the worse signal integrity is.</i>
$SN_difference = (Int_sig) - (Int_ISI) - (Int_xtk)$	<i>The larger value , the better signal integrity is.</i>
$SN_ratio = \frac{Int_sig}{(Int_ISI) + (Int_xtk)}$	The concept is similar to SNR (signal-to-noise ratio) <i>The larger value , the better signal integrity is.</i>

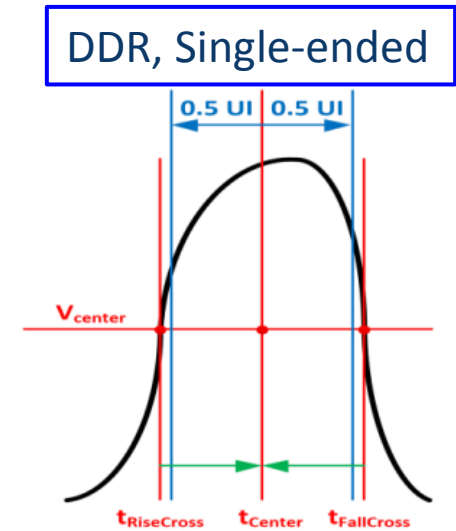
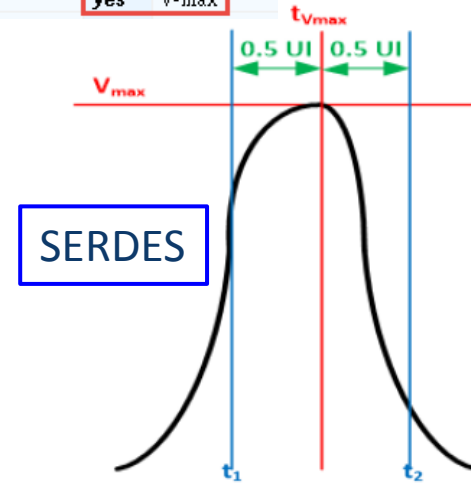
About SRC

Net group names	Tx component	Net name	Passive component	Net name	Passive component	Net name	Rx component(active)	Rx component(standby)	Rx component(not populated)	FIR filter	Pulse center
PCIEX1_TX_PCH1_CN3											
	PCH1	X_PCIEX1_1_TX_N_C	C27	X_PCIEX1_1_TX_N	-	-	CN3	-	-	yes	v-max
	PCH1	X_PCIEX1_1_TX_P_C	C26	X_PCIEX1_1_TX_P	-	-	CN3	-	-	yes	v-max
	PCH1	X_PCIEX1_2_TX_N_C	C25	X_PCIEX1_2_TX_N	-	-	CN3	-	-	yes	v-edge
	PCH1	X_PCIEX1_2_TX_P_C	C24	X_PCIEX1_2_TX_P	-	-	CN3	-	-	yes	v-max
	PCH1	X_PCIEX1_3_TX_N_C	C23	X_PCIEX1_3_TX_N	-	-	CN3	-	-	yes	v-max
	PCH1	X_PCIEX1_3_TX_P_C	C22	X_PCIEX1_3_TX_P	-	-	CN3	-	-	yes	v-max

Net group names	Tx component	Net name	Rx component(active)	Rx component(standby)	Rx component(not populated)	FIR filter	Pulse center
PCIEX1_RX_CN3_PCH1							
	CN3	X_PCIEX1_1_RX_N	PCH1	-	-	yes	v-max
	CN3	X_PCIEX1_1_RX_P	PCH1	-	-	yes	v-max
	CN3	X_PCIEX1_2_RX_N	PCH1	-	-	yes	v-max
	CN3	X_PCIEX1_2_RX_P	PCH1	-	-	yes	v-max
	CN3	X_PCIEX1_3_RX_N	PCH1	-	-	yes	v-max
	CN3	X_PCIEX1_3_RX_P	PCH1	-	-	yes	v-max

✔ FIR filter is recommended to be enabled for SERDES link SI Metrics Check. When FIR is applied:

- Coefficient is calculated for each net by forcing the first post cursor 0
- The pulse is balanced and centered, making the SI Metrics more reasonable (Otherwise, the pulse is not centered, causing large ISI noise)



About SRC

20 ns is typical for SRC analysis whereas something shorter, 5 – 10 ns may be used for a quicker debug run.

The diagram shows a signal waveform with parameters: T_r (rise time), T_w (pulse width), T_f (fall time), T_{period} (period), V_{high} (high voltage), and V_{low} (low voltage).

Interface and ckt type	Tx_term type	R(ohm)	C(F)	V_low(V)	V_high(V)	Tdelay	T_r(s)	T_f(s)	T_w(s)	T_period(s)	Rx_term type	R(ohm)	C(F)	(S)Rx_term type	(S)R(ohm)	(S)C(F)
PCIEX1_RX:SE	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-
PCIEX1_RX:Diff	Parallel RC	50	1p	0	1	0p	60p	60p	140p	1e+012p	Parallel RC	50	1p	-	-	-
PCIEX1_TX:SE	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-
PCIEX1_TX:Diff	Parallel RC	50	1p	0	1	0p	60p	60p	140p	1e+012p	Parallel RC	50	1p	-	-	-

Simulation Options:

- Level-1 (Single lines with ideal PDN; delay, loss, reflection effects)
- Level-2 (Coupled lines with ideal PDN; plus trace, via xtalk effects)
- Level-3 (Coupled lines with non-ideal PDN; plus return path and SSO effects)
- Level-4 (3DFEM model based; lack of reference cases)

Parameters:

- Transient Time Step (ps): 6
- Coupling (%): 2
- Rise Time (ps): 30
- Sim Time: 10 ns

About SRC

Different SI / PI / EMI Levels for Different Needs

SI Metrics Check

Layout Setup

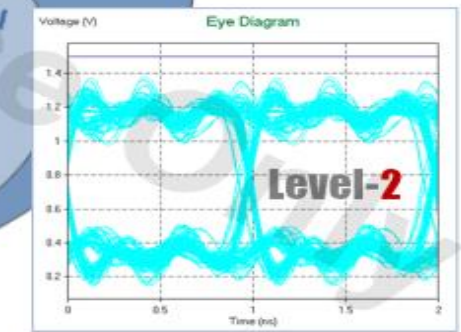
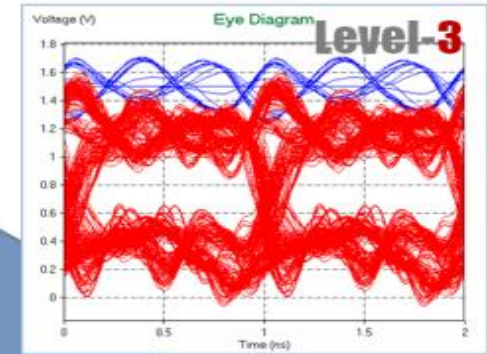
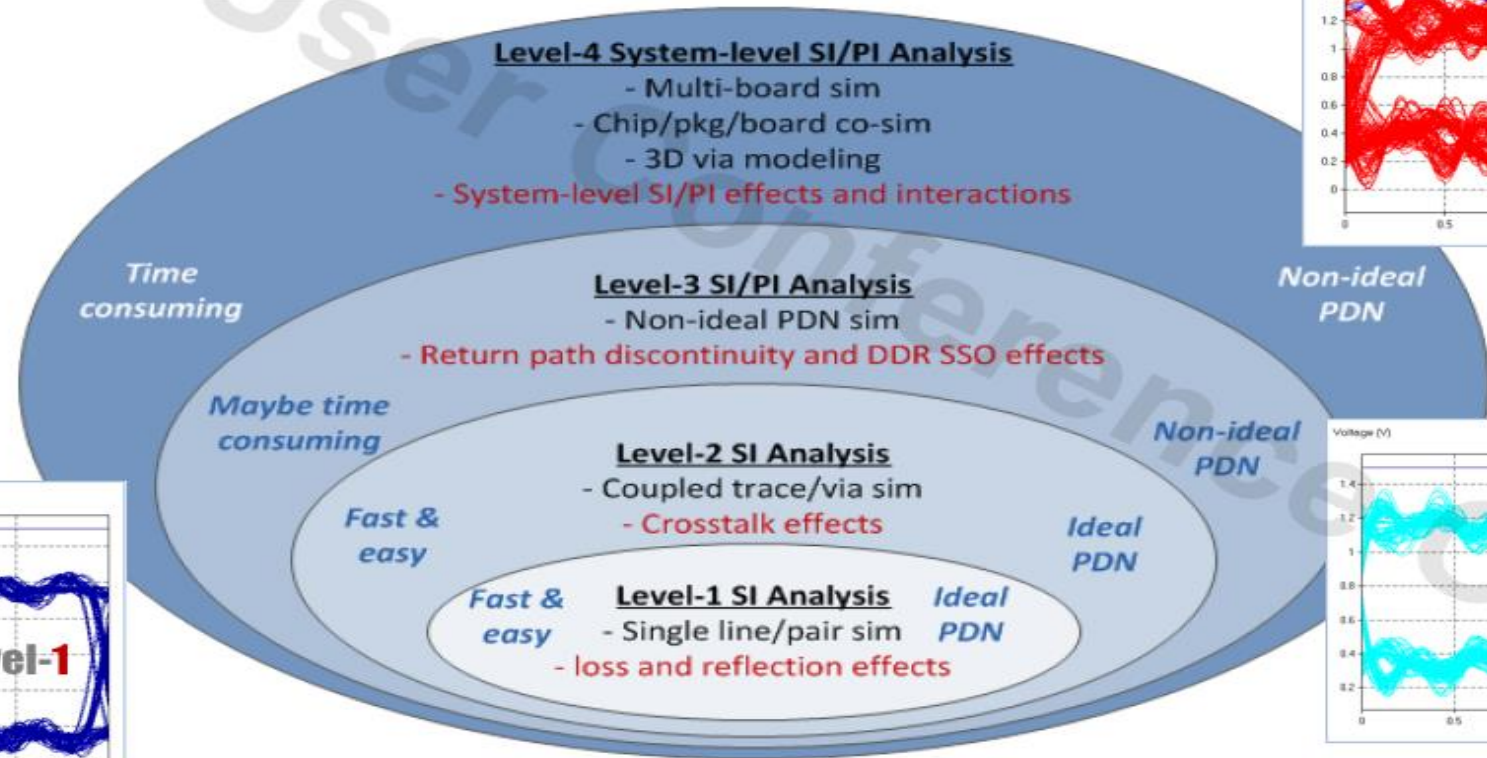
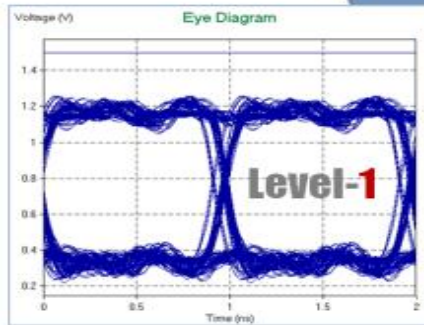
- Load Layout File
- Check Stackup
- Prepare Nets

Set up SI Metrics Simulation

- ✓ Enable SI Metrics Check Mode
- Set up Net Groups
- Set up Models
- Set up Simulation Option
- Cut by Net Groups**
- Save File with Error Check

Simulation

- Start Simulation
- Generate SI Metrics Check Report
- Save SI Metrics Check Report
- Load SI Metrics Check Results



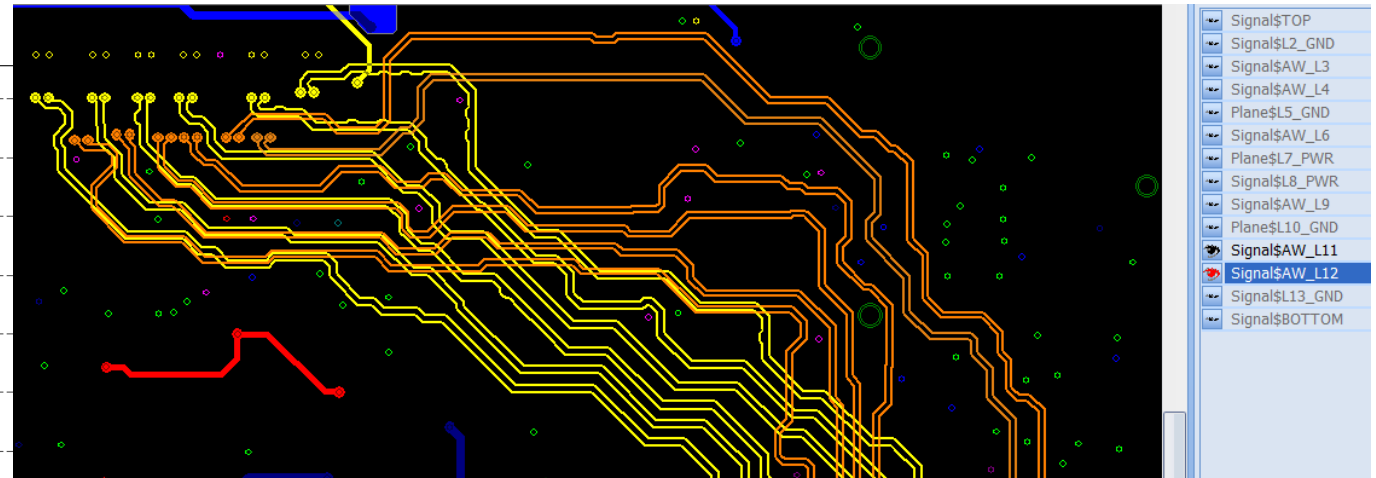
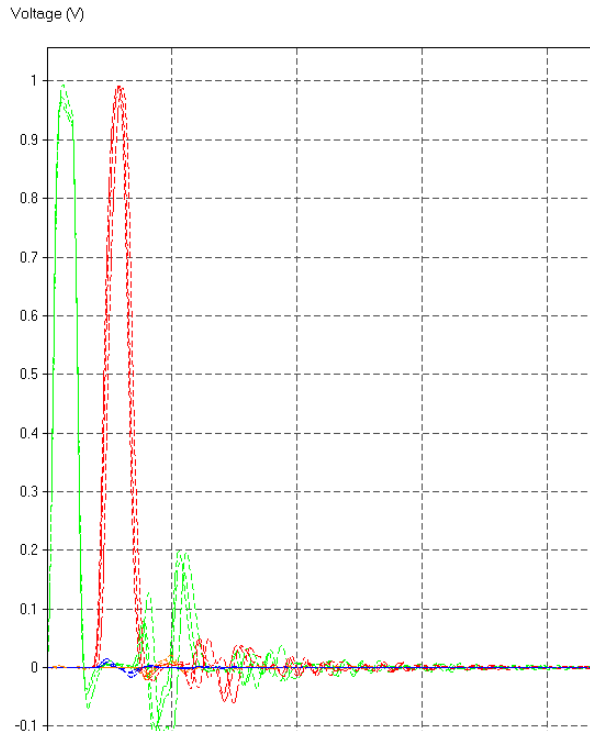
About SRC

Present Curves

- RX
 - PCIEX1_TX_PCH1_CN3
- TX
 - PCIEX1_TX_PCH1_CN3
- FEXT
 - PCIEX1_TX_PCH1_CN3
- NEXT
 - PCIEX1_TX_PCH1_CN3

Loaded Curves

- TD Calc...
- Save...
- Load...
- Load SI Metrics Check Results
- Reverse Name Order
- Load Curve Pattern
- Save Current Patten
- Export to Excel
- Export Top 10 Aggressors to File
- Show Full Names



4.1.1 Performance metrics for net group PCIEX1_TX_PCH1_CN3

Performance metrics **SN_difference** is the most importance value

Net name	INT_Sig (V*ps)	INT_ISI (V*ps)	INT_XTK (V*ps)	SN_difference (V*ps) 6	SN_ratio
X_PCIEX1_2_TX_P	164.92	54.60	4.24	106.09	2.80318
X_PCIEX1_3_TX_P	164.87	55.30	5.05	104.53	2.73216
X_PCIEX1_0_TX_P	162.16	60.84	2.66	98.66	2.55389
X_PCIEX1_4_TX_P	164.37	68.95	0.59	94.83	2.36362
X_PCIEX1_1_TX_P	163.37	60.27	9.45	93.65	2.34312
X_PCIEX1_5_TX_P	162.62	71.33	0.48	90.82	2.26478

If **SN_difference** is lower than the reference and the **INT_XTK** is shown to be higher, use this file to quickly identify and mitigate XTK causes.

About SRC

Using SRC for design that is “out of guideline”:

1. Check the layout by checking electrical performance instead of layout rules.
2. Locate the weakest signal(s) and fix it/them.
3. Check if the next revision of board does have improvement.
4. Understand the risk of current design based on other project(s).
5. Perform quick “what-if” type analysis on an actual implementation.

Good reference design selection:

1. Current version of the design
2. An exiting working design

Abstract

- Overview
- ERC (Electrical Rule Check)
- SRC (Simulation Rule Check)
- **Applications**
- Summary

Applications

With easy setup and fast simulation, ERC enables practical first-order screening of electrical issues before handing off to SI experts for final check.

- **ERC → SRC → Simulation:**

- ✓ Use ERC to screen layout and identify the worst case for further SRC or SI analysis
- ✓ Use SRC to evaluate the SI impact of design rule violations and investigate tradeoffs

- **SRC → ERC:**

- ✓ Use ERC to find out how to fix SI problems shown in SRC or SI simulations

- Compare ERC and SRC results with **known-good reference design** and the part of the design that has **been fully analyzed**.

Applications

General SI Simulation	Trace Impedance/ Coupling Check	SI Performance Metrics Check	DDR Simulation	Time-domain PDN Simulation
<p>Mainstream SI <i>L1/L2 for fast sim</i></p> <p>Easy to setup; Sim runs fast</p> <p>Waveforms & measurements</p>	<p>Geometry based</p> <p>Trace impedance, coupling & reference check for entire board or net groups</p> <p>Results tables; Results plots; Layout overlay; Layout x-probing</p>	<p>Simulation based <i>L1/L2 for fast sim</i> <i>L3 for non-ideal PDN</i></p> <p>Loss, reflection, xtalk check, typically by net groups</p> <p>Waveforms; Xtalk v_max & v_min</p>	<p>Layout-based DDR simulation <i>L1/L2 for fast sim</i> <i>L3 for SSO</i></p> <p>No s-parameter model needed for on-board DRAMs</p> <p>Waveforms & measurements</p>	<p>Layout-based TD PDN sim</p> <p>PDN chip-pkg- board co-sim with <i>-Voltus die mode</i> <i>-XcitePI IO model</i> <i>with die grid</i></p> <p>Voltage / current distributions; dynamic noise propagation</p>

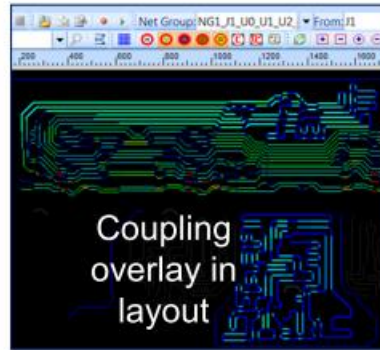
Potential power noise path check (**Treat target power as signal** and use SRC):

- A 3-pin “Source” should be created at the source of the potential noise. Typically at the output of the Voltage Regulator Module (VRM) inductor.
- A 3-pin “Sink” should be created where the current will be consumed.
- These devices will be used as transmit and receive components in the Net Group setup page.

Abstract

- Overview
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Summary



Coupling table

Net	Length (mm)	Coupling Coefficient
A1	156.476	0.444
A2	156.476	0.444
A3	157.880	0.501
A4	228.866	0.474
A5	141.074	0.266
A6	157.349	0.233
A7	155.712	0.238
A8	157.213	0.290
A9	158.052	0.249
A10	155.802	0.263
A11	141.108	0.267
A12	156.902	0.264
A13	157.052	0.419
A14	157.066	0.274
A15	158.146	0.197

ERC

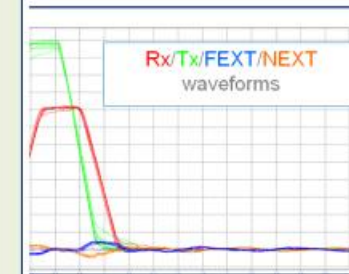
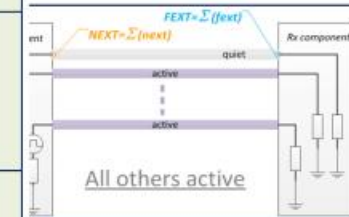
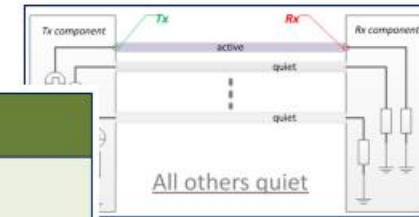
Electrical rule check

Trace Impedance/Coupling Check
Geometry-based
Micro, individual, segment-level view (coupling %, Ω & mm)
Options Check all nets Check selected nets Check nets in net groups
Results Coupling coefficient Impedance Trace reference Summary & detailed tables Expanded & collapsed plots Layout overlay Layout cross probing HTML report

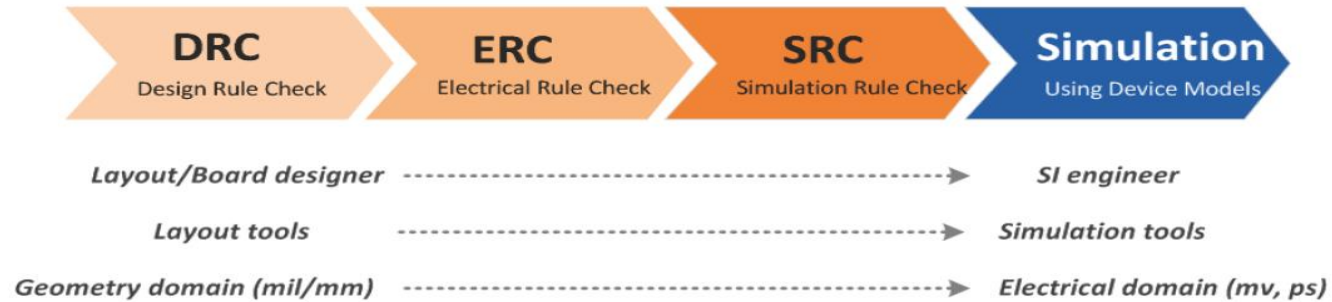
SRC

Simulation rule check

SI Metrics Check
Simulation-based
Macro, combined net-level , view (mv & ps)
Options Level-1 simulation Level-2 simulation Level-3 simulation
Results Waveforms: Tx / Rx / NEXT / FEXT v_min & v_max SI performance metrics HTML report



Summary



- DRC's alone cannot validate the interconnects **electrical characteristics**.
 - Examples: signals crossing split or different reference planes causing impedance changes.
- ERC: **Segment-level** view to shows why low performance happened and how to fix it .
- SRC: **Net-level view** to shows what happened and its effect on performance.
- ERC/SRC designed for use by the **PCB layout designer**, not the signal integrity (SI) expert.
 - SI Expert can focus on other complex problems such as “**stackup design**”, “**design guide creation**”, “**constraint setting**”, “**risk assessment proposal**”, “**design improvement**”, “**suggestion/solution/explanation for customers**”.
 - The possibility in catching something which might be missed in the traditional layout review is valuable, which may decrease the effort in the validation phase.



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